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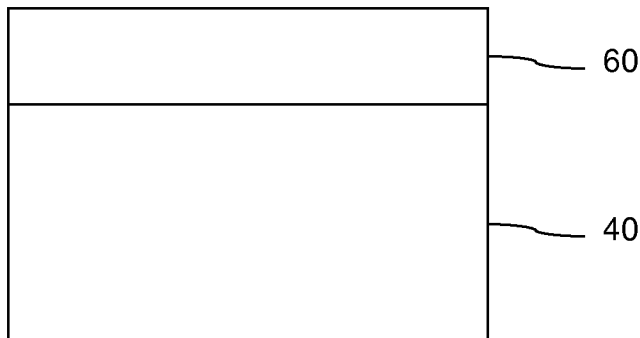
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(54) Title: PROCESS FOR MAKING A GAN SUBSTRATE



(57) Abstract: The invention relates to a process for making a GaN substrate (60), characterized in that it comprises the following steps: (a) transferring a first monocrystal GaN layer (50) onto a supporting substrate (40); (b) applying crystal growth for a second monocrystal GaN layer on the first layer (50); the first and second GaN layers thereby forming together said GaN substrate (60), said GaN substrate (60) having a thickness of at least 10 micrometers, (c) removing at least one portion of the supporting substrate (40).



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